

M5M5408BFP/TP/RT/KV/KR

PRELIMINARY

Notice: This is not a final specification.
Some parametric limits are subject to change

4194304-BIT (524288-WORD BY 8-BIT) CMOS STATIC RAM

DESCRIPTION

The M5M5408B is a family of 4-Mbit static RAMs organized as 524,288-words by 8-bit, fabricated by Mitsubishi's high-performance 0.25μm CMOS technology.

The M5M5408B is suitable for memory applications where a simple interfacing, battery operating and battery backup are the important design objectives.

M5M5408B is packaged in 32-pin plastic SOP, 32-pin plastic TSOP and 32-pin 8mm x 13.4mm STSOP packages. Two types of TSOPs and two types of STSOPs are available, M5M5408BTP (normal-lead-bend TSOP), M5M5408BRT (reverse-lead-bend TSOP), M5M5408BKV (normal-lead-bend STSOP) and M5M5408BKR (reverse-lead-bend STSOP). These two types TSOPs and two types STSOPs are suitable for a surface mounting on double-sided printed circuit boards.

From the point of operating temperature, the family is divided into three versions; "Standard", "W-version", and "I-version". Those are summarized in the part name table below.

FEATURES

- Single +5V power supply
- Small stand-by current: 0.4μA(3V,typ.)
- No clocks, No refresh
- Data retention supply voltage=2.0V to 5.5V
- All inputs and outputs are TTL compatible.
- Easy memory expansion by \bar{S}
- Common Data I/O
- Three-state outputs: OR-tie capability
- \overline{OE} prevents data contention in the I/O bus
- Process technology: 0.25μm CMOS
- Package:
 - M5M5408BFP: 32 pin 525 mil SOP
 - M5M5408BTP/RT: 32 pin 400 mil TSOP(II)
 - M5M5408BKV/KR: 32 pin 8mm x 13.4mm STSOP

PART NAME TABLE

Version, Operating temperature	Part name (## stands for "FP", "TP", "RT", "KV" or "KR")	Power Supply	Access time max.	Stand-by current I _{cc(PD)} , V _{cc} =3.0V			Active current I _{cc1} (5.0V, typ.)
				typical *	Ratings (max.)		
					25°C	70°C	
Standard 0 ~ +70°C	M5M5408B## -55L	5.0V	55ns	---	50μA	---	50mA (10MHz)
	M5M5408B## -70L		70ns				
	M5M5408B## -10L		100ns				
	M5M5408B## -55H	5.0V	55ns	0.4μA	10μA	---	
	M5M5408B## -70H		70ns				
	M5M5408B## -10H		100ns				
W-version -20 ~ +85°C	M5M5408B## -55LW	5.0V	55ns	---	---	100μA	25mA (1MHz)
	M5M5408B## -70LW		70ns				
	M5M5408B## -10LW		100ns				
	M5M5408B## -55HW	5.0V	55ns	0.4μA	---	20μA	
	M5M5408B## -70HW		70ns				
	M5M5408B## -10HW		100ns				
I-version -40 ~ +85°C	M5M5408B## -55LI	5.0V	55ns	---	---	100μA	
	M5M5408B## -70LI		70ns				
	M5M5408B## -10LI		100ns				
	M5M5408B## -55HI	5.0V	55ns	0.4μA	---	20μA	
	M5M5408B## -70HI		70ns				
	M5M5408B## -10HI		100ns				

* "typical" parameter is sampled, not 100% tested.

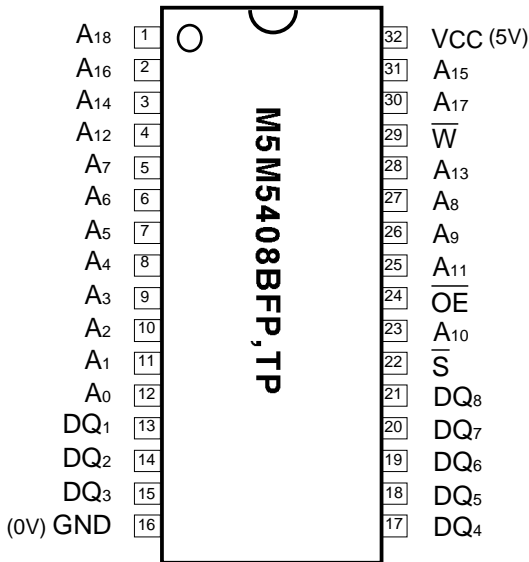
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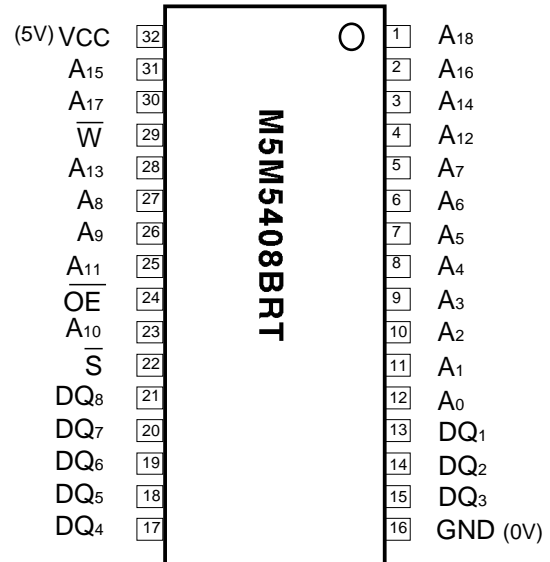
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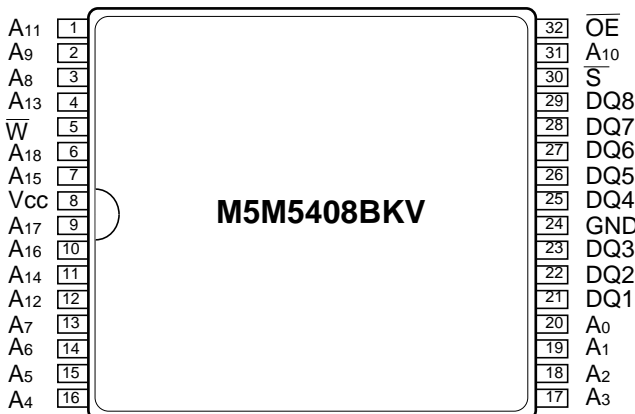
PIN CONFIGURATION (TOP VIEW)



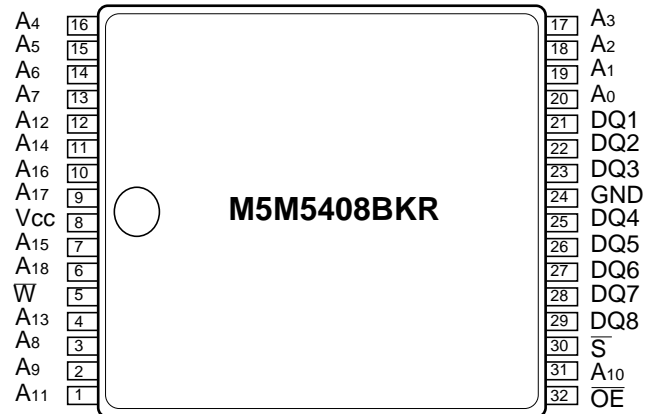
Outline 32P2M-A (FP)
32P3Y-H (TP)



Outline 32P3Y-J (RT)



Outline 32P3K-B



Outline 32P3K-C

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FUNCTION

The M5M5408BFP,TP,RT,KV,KR is organized as 524,288-words by 8-bit. These devices operate on a single +5.0V power supply, and are directly TTL compatible to both input and output. Its fully static circuit needs no clocks and no refresh, and makes it useful.

A write operation is executed during the \bar{S} low and \bar{W} low overlap time. The address(A0~A18) must be set up before the write cycle

A read operation is executed by setting \bar{W} at a high level and OE at a low level while S are in an active state($\bar{S}=L$).

When setting \bar{S} at a high level, the chips are in a non-selectable mode in which both reading and writing are disabled. In this mode, the output stage is in a high-impedance state, allowing OR-tie with other chips. Setting the \bar{OE} at a high level, the output stage is in a high-impedance state, and the data bus contention problem in the write cycle is eliminated.

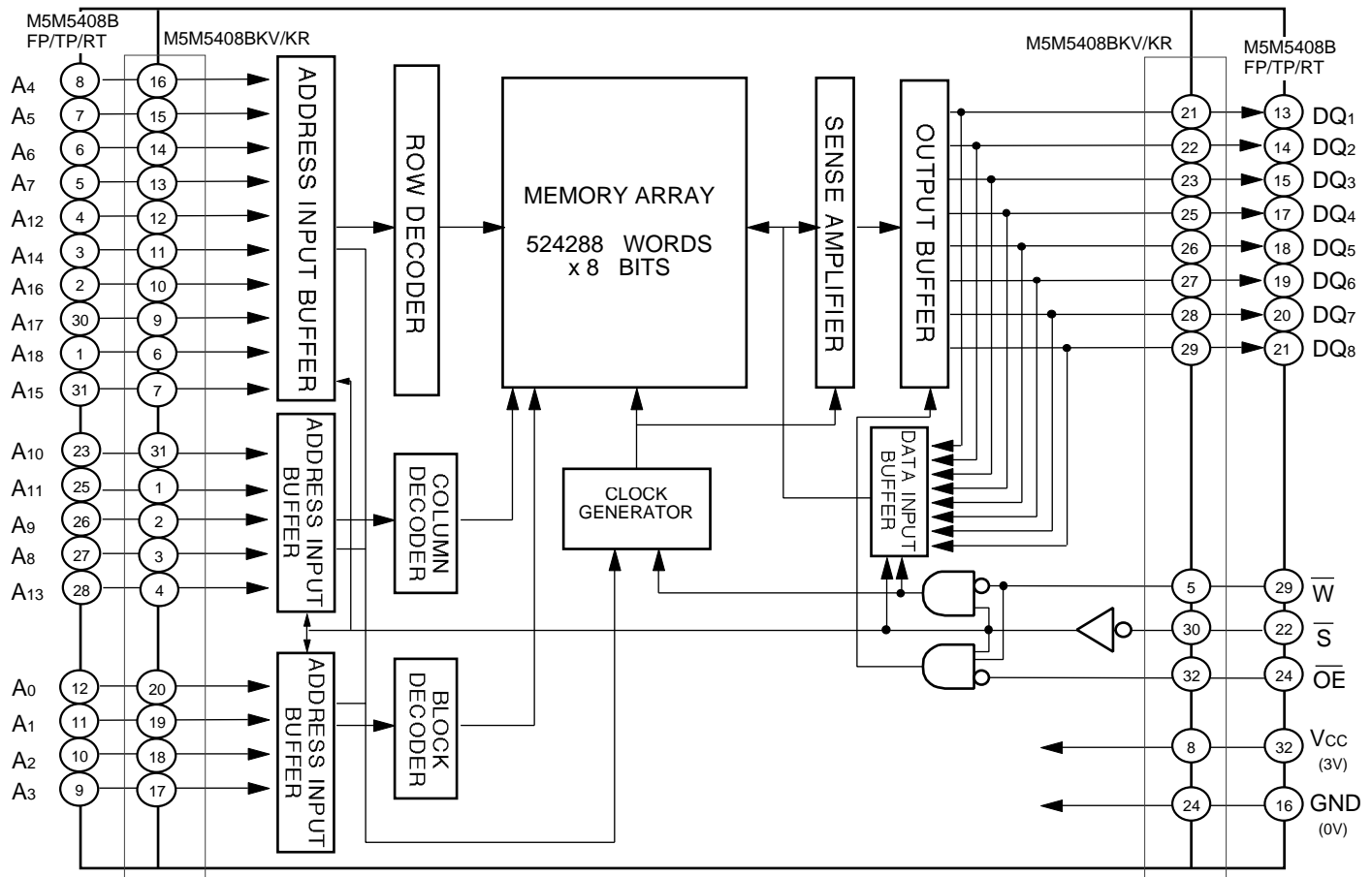
The power supply current is reduced as low as 0.4 μ A(25°C, typical), and the memory data can be held at +2V power supply, enabling battery back-up operation during power failure or power-down operation in the non-selected mode.

FUNCTION TABLE

\bar{S}	\bar{W}	\bar{OE}	Mode	DQ	I _{cc}
H	X	X	Non selection	High-impedance	Standby
L	L	X	Write	Data input (D)	Active
L	H	L	Read	Data output (Q)	Active
L	H	H	Read	High-impedance	Active

Pin	Function
A0 ~ A18	Address input
DQ1 ~ DQ8	Data input / output
\bar{S}	Chip select input
\bar{W}	Write control input
\bar{OE}	Output inable input
V _{cc}	Power supply
GND	Ground supply

BLOCK DIAGRAM



M5M5408BFP/TP/RT/KV/KR**PRELIMINARY**Notice: This is not a final specification.
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Symbol	Parameter	Conditions	Ratings	Units
V _{CC}	Supply voltage	With respect to GND	-0.3* ~ +7	V
V _I	Input voltage	With respect to GND	-0.3* ~ V _{CC} + 0.3	
V _O	Output voltage	With respect to GND	0 ~ V _{CC}	
P _d	Power dissipation	T _a =25°C	700	mW
T _a	Operating temperature	Standard (-L, -H)	0 ~ +70	°C
		W-version (-LW, -HW)	-20 ~ +85	
		I-version (-LI, -HI)	-40 ~ +85	
T _{stg}	Storage temperature		-65 ~ 150	°C

* -3.0V in case of AC (Pulse width 30ns)

DC ELECTRICAL CHARACTERISTICS(V_{CC}=5V±10%, unless otherwise noted)

Symbol	Parameter	Conditions	Limits			Units	
			Min	Typ	Max		
V _{IH}	High-level input voltage		2.2		V _{CC} +0.3V	V	
V _{IL}	Low-level input voltage		-0.3*		0.8		
V _{OH1}	High-level output voltage 1	I _{OH} = -1mA	2.4				
V _{OH2}	High-level output voltage 2	I _{OH} = -0.1mA	V _{CC} -0.5V				
V _{OL}	Low-level output voltage	I _{OL} =2mA			0.4		
I _I	Input leakage current	V _I =0 ~ V _{CC}			±1	μA	
I _O	Output leakage current	$\bar{S}=V_{IH}$ or $\bar{OE}=V_{IH}$, V _{I/O} =0 ~ V _{CC}			±1		
I _{CC1}	Active supply current (AC, MOS level)	\bar{S} 0.2V Output-open Other inputs 0.2V or V _{CC} -0.2V	minimum cycle	-	50	80	mA
			f= 1MHz	-	25	30	
I _{CC2}	Active supply current (AC, TTL level)	$\bar{S}=V_{IL}$ Output-open Other inputs=V _{IH} or V _{IL}	minimum cycle	-	60	90	
			f= 1MHz	-	30	40	
I _{CC3}	Stand by supply current (AC, MOS level)	\bar{S} V _{CC} -0.2V Other inputs=0~V _{CC}	-LW, -LI	-	-	200	μA
			-L	-	-	100	
			-HW, -HI	-	0.4	40	
			-H	-	0.4	20	
I _{CC4}	Stand by supply current (AC, TTL level)	$\bar{S}=V$,Other inputs= 0 ~ V _{CC}	-	-	3	mA	

Note 1: Direction for current flowing into IC is indicated as positive (no mark)

* -3.0V in case of AC (Pulse width 50ns)

Note 2: Typical value is for V_{CC}=5.0V and T_a=25°C**CAPACITANCE**(V_{CC}=5.0V±10%, unless otherwise noted)

Symbol	Parameter	Conditions	Limits			Units
			Min	Typ	Max	
C _I	Input capacitance	V _I =GND, V _I =25mVrms, f=1MHz			8	pF
C _O	Output capacitance	V _O =GND, V _O =25mVrms, f=1MHz			10	



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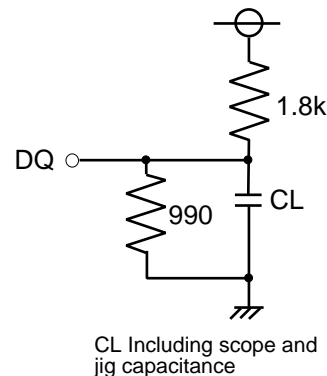
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AC ELECTRICAL CHARACTERISTICS (V_{CC}=5.0V±10%, unless otherwise noted)

(1) TEST CONDITIONS

Supply voltage	5.0V
Input pulse	V _{IH} =2.4V, V _{IL} =0.6V (FP,TP,RT,KV,KR-70,-10) V _{IH} =3.0V, V _{IL} =0V (FP,TP,RT,KV,KR-55)
Input rise time and fall time	5ns
Reference level	V _{OH} =V _{OL} =1.5V Transition is measured ±500mV from steady state voltage. (for t _{en} , t _{dis})
Output loads	Fig.1, CL=100pF (FP,TP,RT,KV,KR-70,-10) CL=30pF (FP,TP,RT,KV,KR-55) CL=5pF (for t _{en} , t _{dis})



CL Including scope and jig capacitance

Fig.1 Output load

(2) READ CYCLE

Symbol	Parameter	Limits						Units
		M5M5408BFP,TP,RT, KV,KR-55		M5M5408BFP,TP,RT, KV,KR-70		M5M5408BFP,TP,RT, KV,KR-10		
		Min	Max	Min	Max	Min	Max	
t _{CR}	Read cycle time	55		70		100		ns
t _{a(A)}	Address access time		55		70		100	ns
t _{a(S)}	Chip select access time		55		70		100	ns
t _{a(OE)}	Output enable access time		25		35		50	ns
t _{dis(S)}	Output disable time after \bar{S} high		20		25		35	ns
t _{dis(OE)}	Output disable time after \overline{OE} high		20		25		35	ns
t _{en(S)}	Output enable time after \bar{S} low	10		10		10		ns
t _{en(OE)}	Output enable time after \overline{OE} low	5		5		5		ns
t _{v(A)}	Data valid time after address	10		10		10		ns

(3) WRITE CYCLE

Symbol	Parameter	Limits						Units
		M5M5408BFP,TP,RT, KV,KR-55		M5M5408BFP,TP,RT, KV,KR-70		M5M5408BFP,TP,RT, KV,KR-10		
		Min	Max	Min	Max	Min	Max	
t _{cw}	Write cycle time	55		70		100		ns
t _{w(W)}	Write pulse width	40		50		60		ns
t _{su(A)}	Address set up time	0		0		0		ns
t _{su(A-WH)}	Address set up time with respect to \bar{W} high	50		60		80		ns
t _{su(S)}	Chip select set up time	50		60		80		ns
t _{su(D)}	Data set up time	25		30		35		ns
t _{h(D)}	Data hold time	0		0		0		ns
t _{rec(W)}	Write recovery time	0		0		0		ns
t _{dis(W)}	Output disable time after \bar{W} low		20		25		35	ns
t _{dis(OE)}	Output disable time after \overline{OE} high		20		25		35	ns
t _{en(W)}	Output enable time after \bar{W} high	5		5		5		ns
t _{en(OE)}	Output enable time after \overline{OE} low	5		5		5		ns

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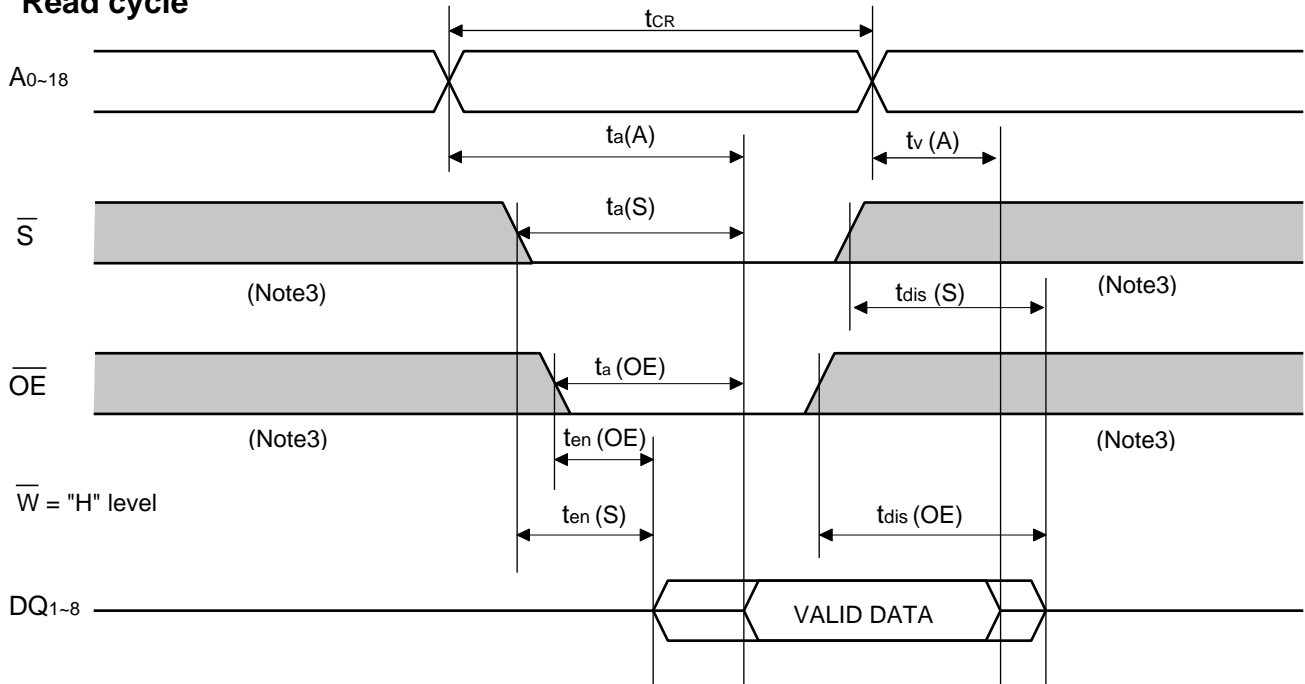
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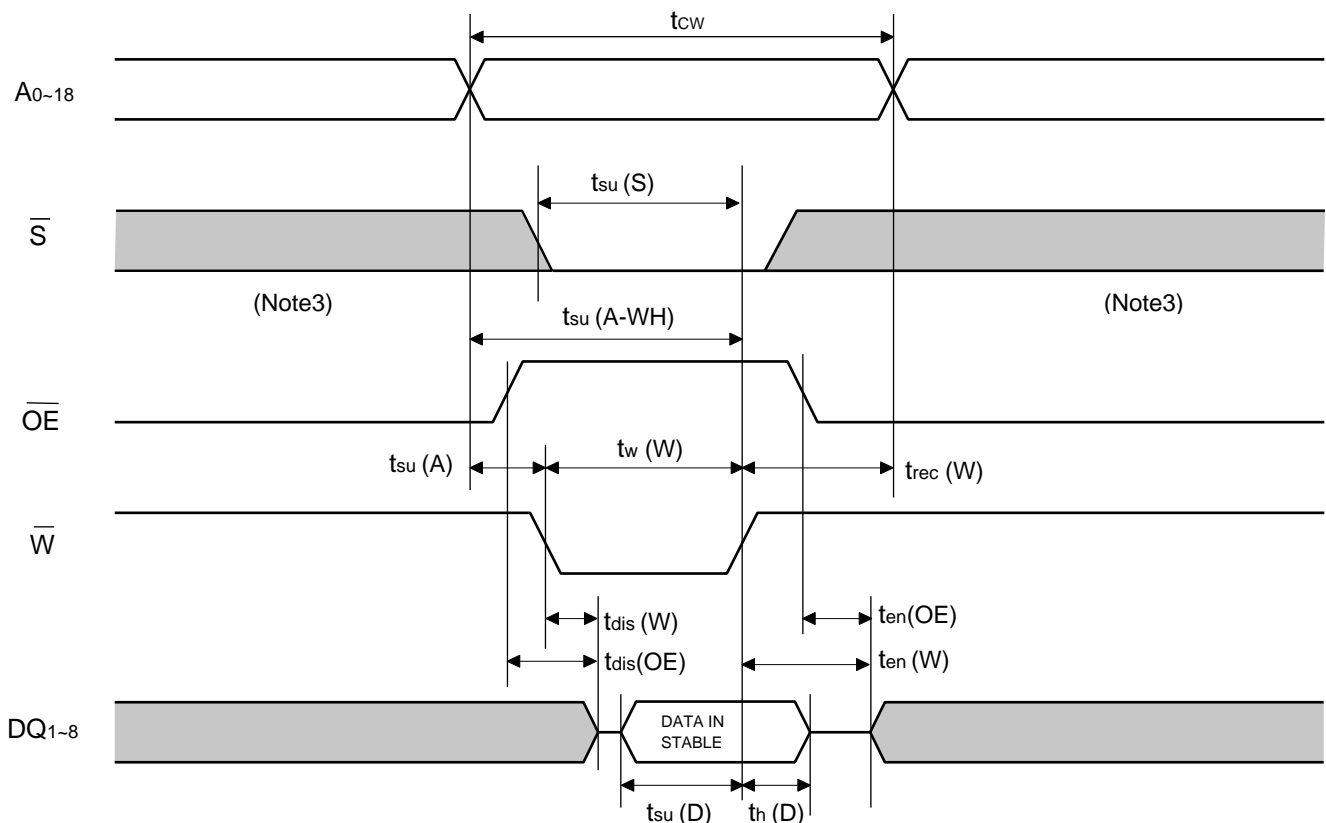
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(4)TIMING DIAGRAMS

Read cycle



Write cycle (\bar{W} control mode)



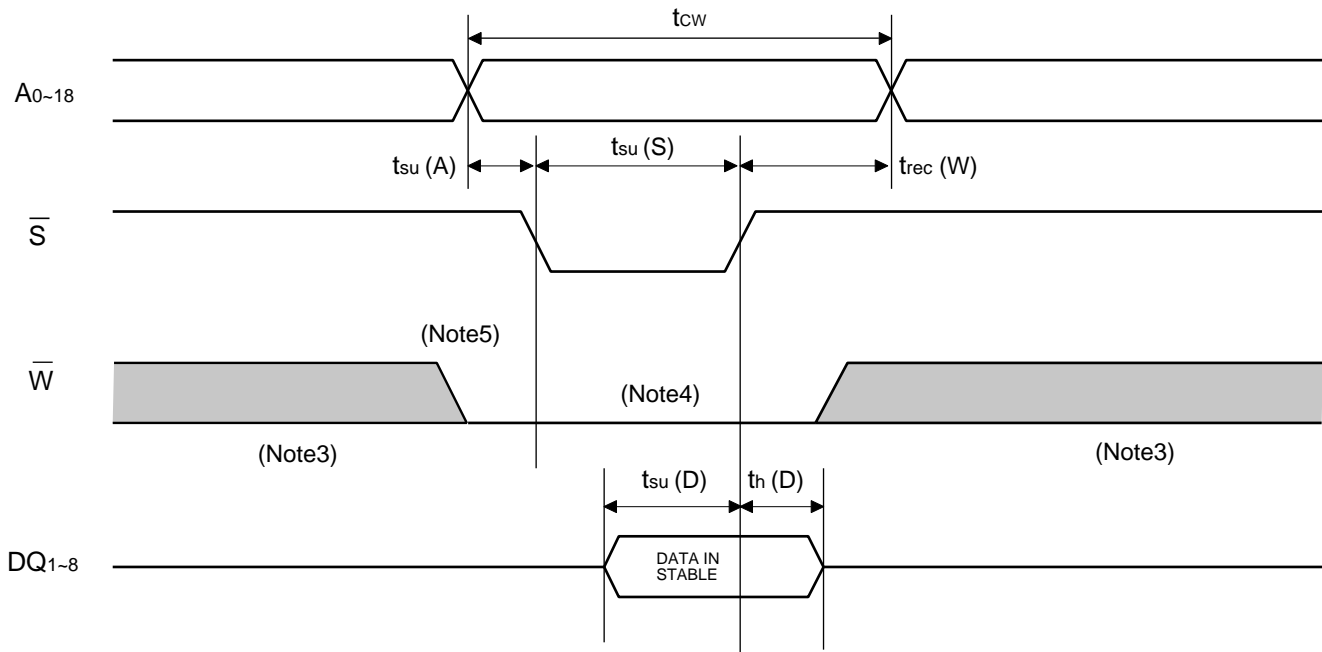
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Write cycle (\overline{S} control mode)



Note 3: Hatching indicates the state is "don't care".

Note 4: A Write occurs during the overlap of a low \overline{S} and a low \overline{W} .

Note 5: If \overline{W} goes low simultaneously with or prior to \overline{S} , the output remains in the high impedance state.

Note 6: Don't apply inverted phase signal externally when DQ pin is in output mode.

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POWER DOWN CHARACTERISTICS

(1) ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test conditions	Limits			Units	
			Min	Typ.	Max		
V _{cc} (PD)	Power down supply voltage		2	-	-	V	
V _I (\bar{S})	Chip select input \bar{S}	V _{cc} (PD) 2.2V	2.2	-	-	V	
		2.2V V _{cc} (PD) 2.0V	-	V _{cc} (PD)	-	V	
I _{cc} (PD)	Power down supply current	V _{cc} =3.0V, \bar{S} V _{cc} -0.2V, Other inputs=0 ~ V _{cc}	-LW, -LI	-	-	100	μA
			-L	-	-	50	μA
			-HW, -HI	-	0.4	20	μA
			-H	-	0.4	10	μA

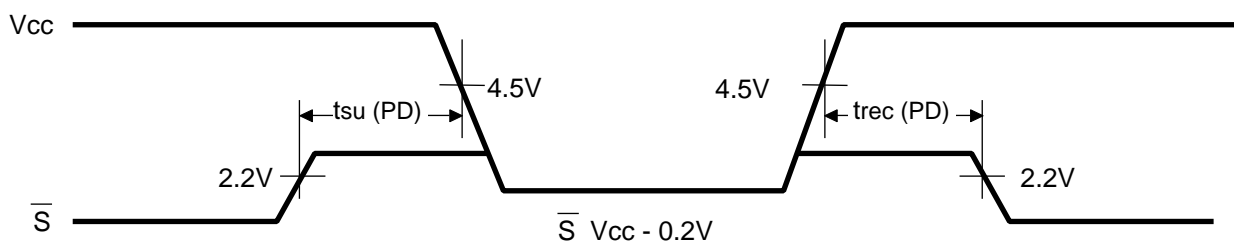
Typical value is for T_a=25°C

(2) TIMING REQUIREMENTS

Symbol	Parameter	Test conditions	Limits			Units
			Min	Typ	Max	
t _{su} (PD)	Power down set up time		0			ns
t _{rec} (PD)	Power down recovery time		5			ms

(3) TIMING DIAGRAM

\bar{S} control mode



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Revision History

<u>Revision No.</u>	<u>History</u>	<u>Date</u>	
K0.1e	The first edition	'98.7.30	Preliminary